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MR3029-81  
Appl. No. 10/714,649  
Reply to Office action of May 06, 2005



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Appl. No. : 10/714,649  
Applicant : Shangir Gwo  
Filed : November 18, 2003  
TC/A.U. : 2818  
Examiner : Dung A. LE  
Title : METHOD FOR GROWING GROUP-III NITRIDE  
SEMICONDUCTOR HETEROSTRUCTURE  
ON SILICON SUBSTRATE

**AMENDMENT AND RESPONSE**

Commissioner for Patent  
P. O. Box 1450  
Alexandria VA 22313-1450

Sir:

In response to the Office Action of May 06, 2005, please amend the above-identified application as follows:

**Amendments to the Specification** begin on Page 2 of this paper

**Amendments to the Claims** are reflected in the listing of claims, which begins on Page 19 of this paper.

**Remarks/Arguments** begin on Page 24 of this paper.